



RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN - PCS/cellular radio and WLL applications.

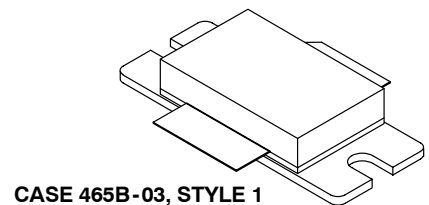
- Typical 2-carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 1200$ mA, $P_{out} = 30$ Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
 Power Gain — 15.5 dB
 Drain Efficiency — 27.5%
 IM3 @ 10 MHz Offset — -37 dBc in 3.84 MHz Channel Bandwidth
 ACPR @ 5 MHz Offset — -41 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 140 Watts CW Output Power

Features

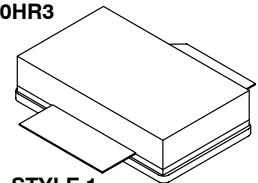
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- Low Gold Plating Thickness on Leads, 40 μ m Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF6S21140HR3
MRF6S21140HSR3

2110-2170 MHz, 30 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465B-03, STYLE 1
NI-880
MRF6S21140HR3



CASE 465C-02, STYLE 1
NI-880S
MRF6S21140HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	P_D	500 2.9	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 80 $^\circ\text{C}$, 140 W CW Case Temperature 75 $^\circ\text{C}$, 30 W CW	$R_{\theta JC}$	0.35 0.38	$^\circ\text{C}/\text{W}$

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\ \mu\text{Adc}$)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 1200\text{ mAdc}$)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	$V_{DS(on)}$	—	0.21	0.3	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	g_{fs}	—	7.2	—	S

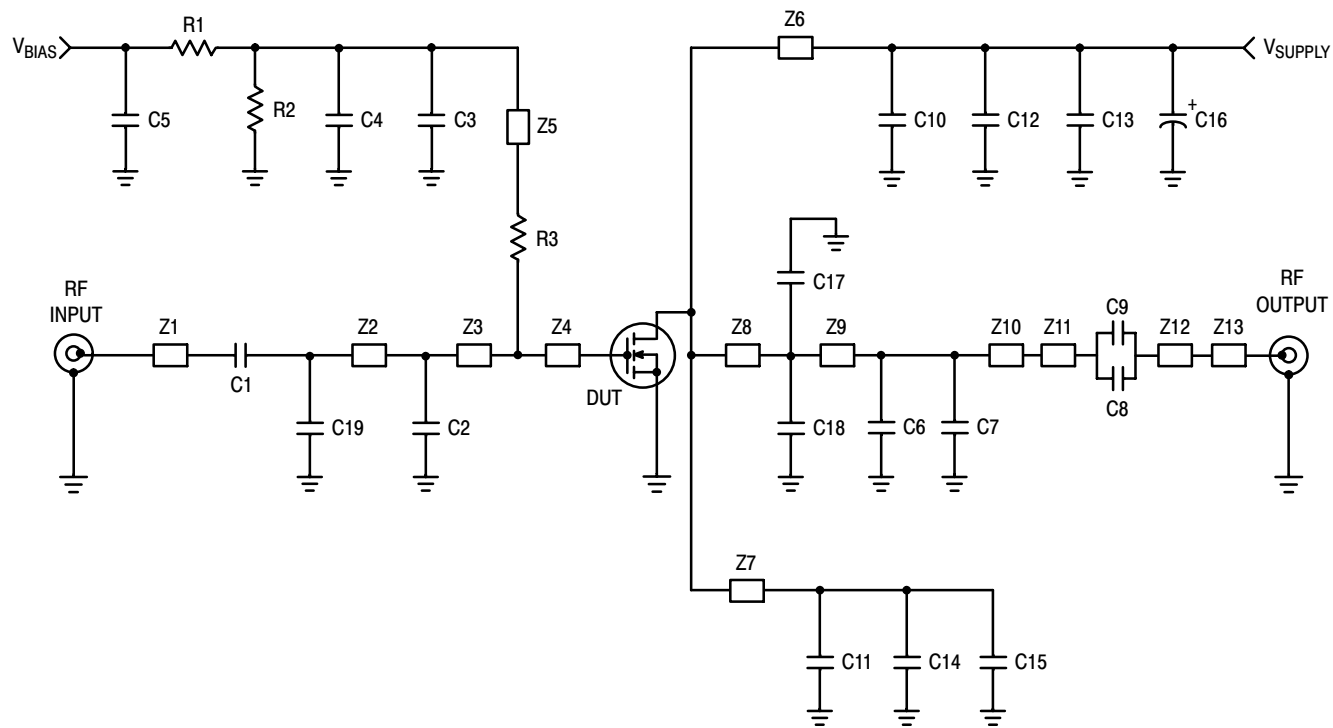
Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2	—	pF
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Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1200\text{ mA}$, $P_{out} = 30\text{ W Avg.}$, $f_1 = 2112.5\text{ MHz}$, $f_2 = 2122.5\text{ MHz}$ and $f_1 = 2157.5\text{ MHz}$, $f_2 = 2167.5\text{ MHz}$, 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset. IM3 measured in 3.84 MHz Channel Bandwidth @ $\pm 10\text{ MHz}$ Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	14.5	15.5	17.5	dB
Drain Efficiency	η_D	26	27.5	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-41	-38	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. Part is internally matched both on input and output.



Z1	0.250" x 0.083" Microstrip	Z8	0.531" x 1.000" Microstrip
Z2	1.177" x 0.083" Microstrip	Z9	0.308" x 0.083" Microstrip
Z3	0.443" x 0.083" Microstrip	Z10	0.987" x 0.083" Microstrip
Z4	0.276" x 0.787" Microstrip	Z11, Z12	0.070" x 0.220" Microstrip
Z5	0.786" x 0.083" Microstrip (quarter wave length for bias purpose)	Z13	0.160" x 0.083" Microstrip
Z6, Z7	0.833" x 0.083" Microstrip (quarter wave length for supply purpose)	PCB	Taconic TLX8-0300, 0.030", $\epsilon_r = 2.55$

Figure 1. MRF6S21140HR3(HSR3) Test Circuit Schematic

Table 5. MRF6S21140HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C3, C8, C9, C10, C11	6.8 pF 100B Chip Capacitors	100B6R8CW	ATC
C2	0.8 pF 100B Chip Capacitor	100B0R8BW	ATC
C4	220 nF Chip Capacitor (1812)	1812Y224KXA	Vishay - Vitramon
C5, C12, C13, C14, C15	10 μ F Chip Capacitors (2220)	C5750X5R1H106MT	TDK
C6, C19	0.2 pF 100B Chip Capacitors	100B0R2BW	ATC
C7	0.5 pF 100B Chip Capacitor	100B0R5BW	ATC
C16	220 μ F, 63 V Electrolytic Capacitor, Radial	13668221	Philips
C17, C18	0.1 pF 100B Chip Capacitors	100B0R1BW	ATC
R1, R2	10 k Ω , 1/4 W Chip Resistors (1206)		
R3	10 Ω , 1/4 W Chip Resistor (1206)		

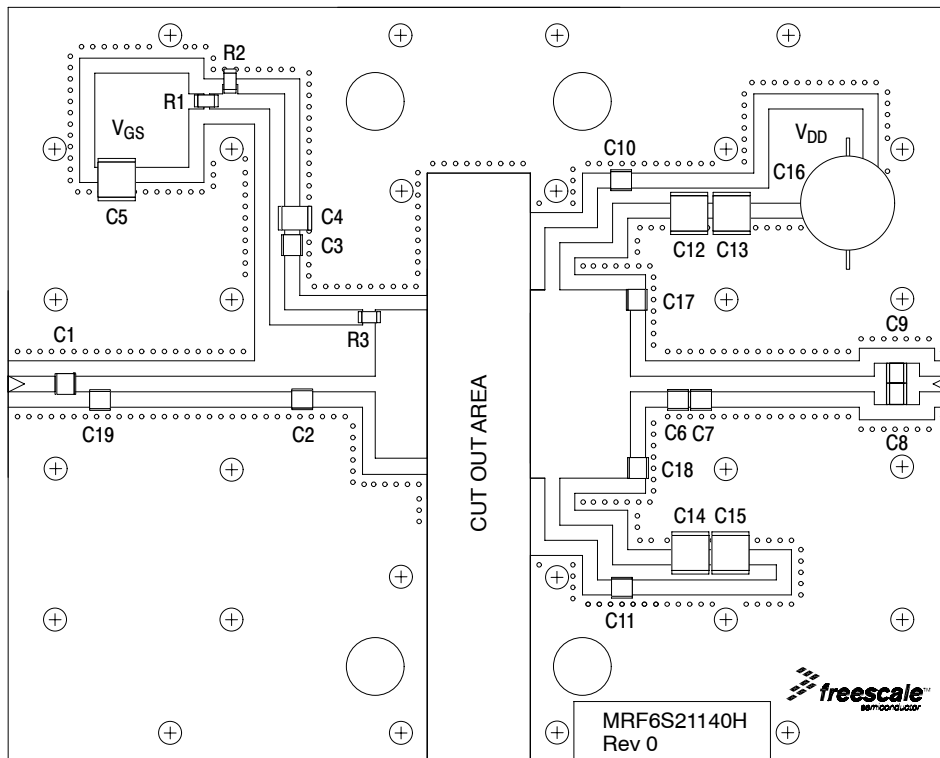


Figure 2. MRF6S21140HR3(HSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

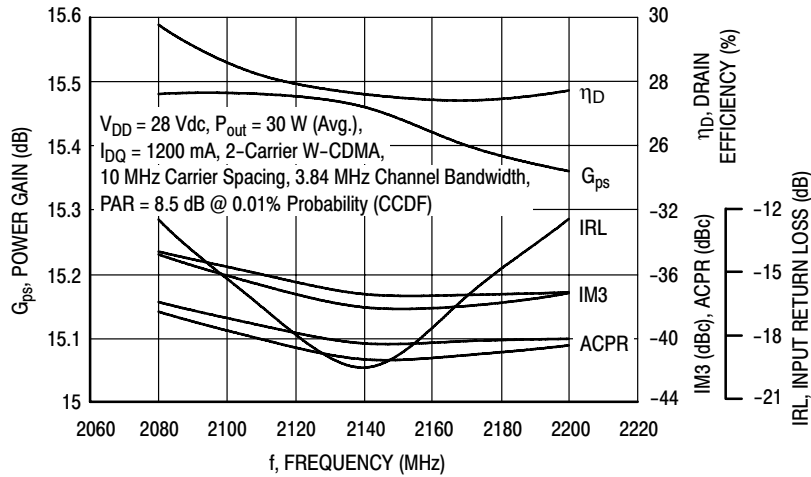


Figure 3. 2-Carrier W-CDMA Broadband Performance @ $P_{out} = 30$ Watts Avg.

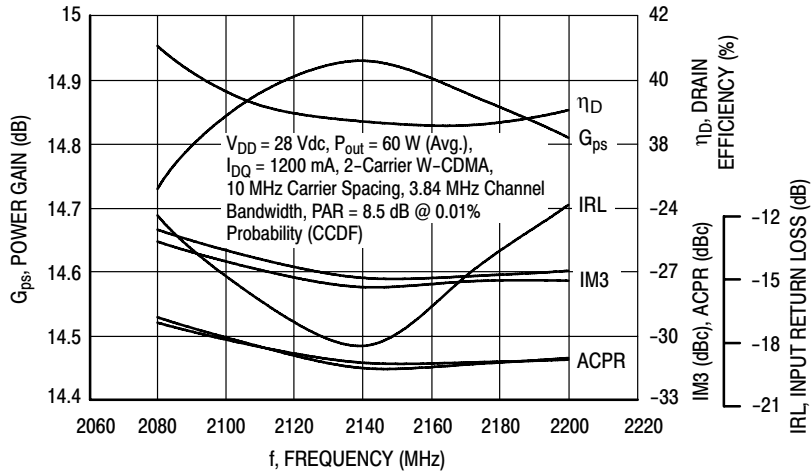


Figure 4. 2-Carrier W-CDMA Broadband Performance @ $P_{out} = 60$ Watts Avg.

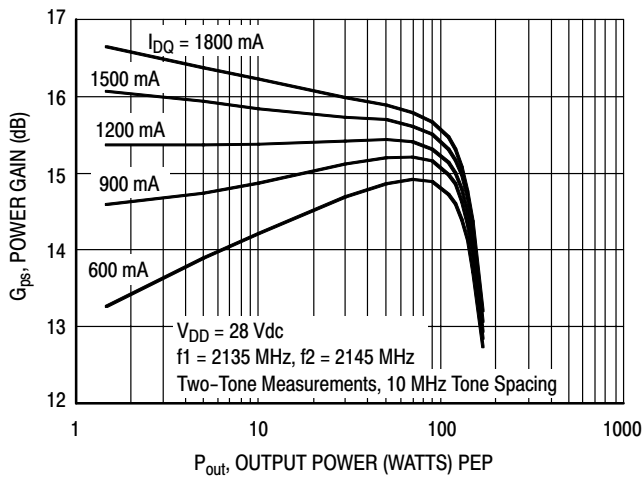


Figure 5. Two-Tone Power Gain versus Output Power

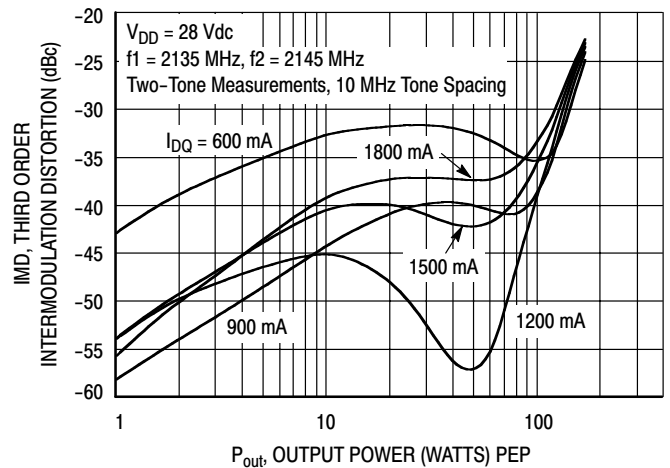


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

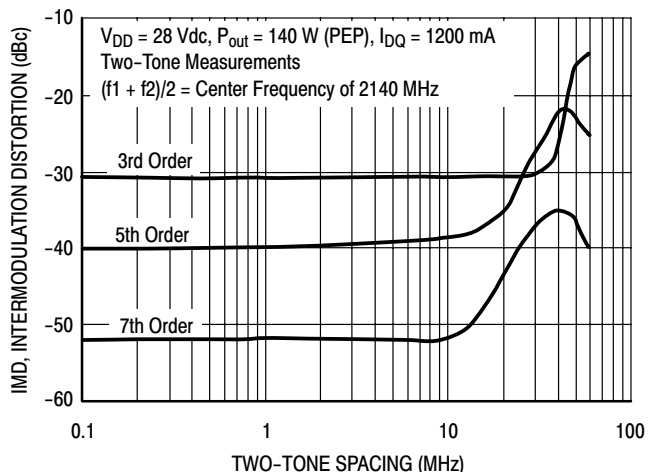


Figure 7. Intermodulation Distortion Products versus Tone Spacing

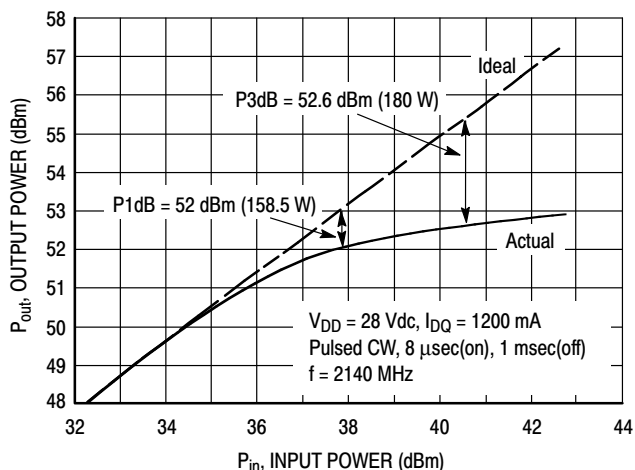


Figure 8. Pulse CW Output Power versus Input Power

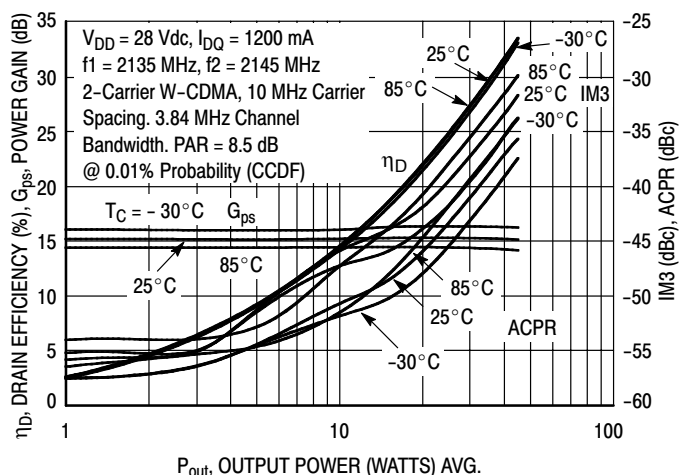


Figure 9. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

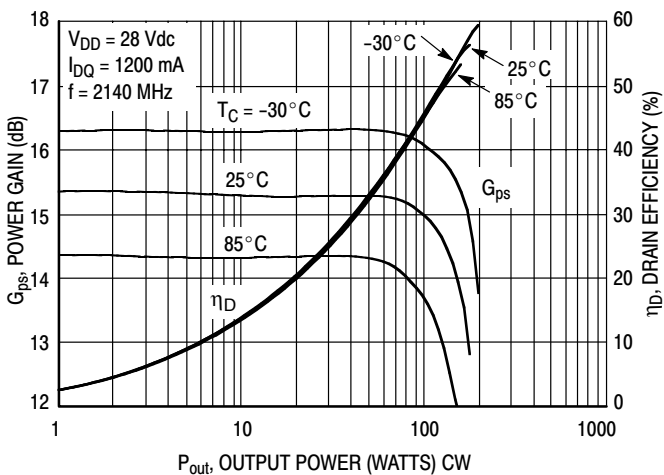


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

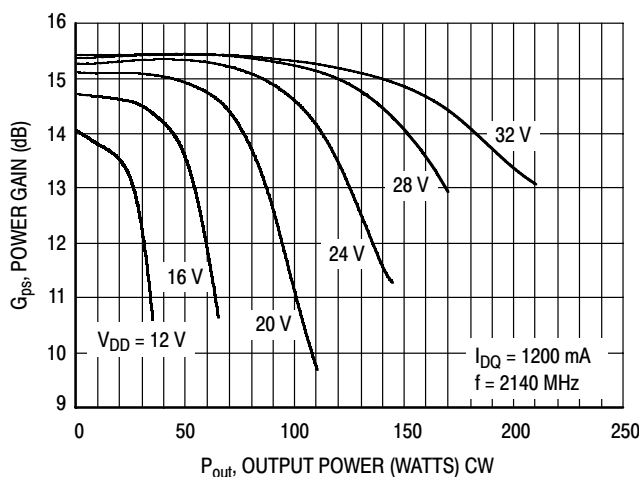
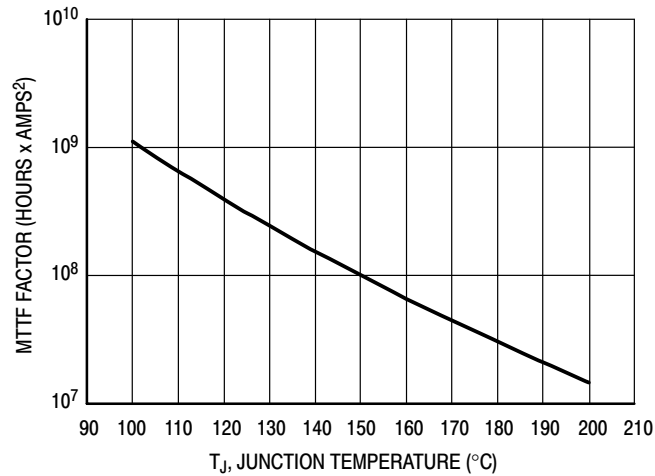


Figure 11. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 12. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

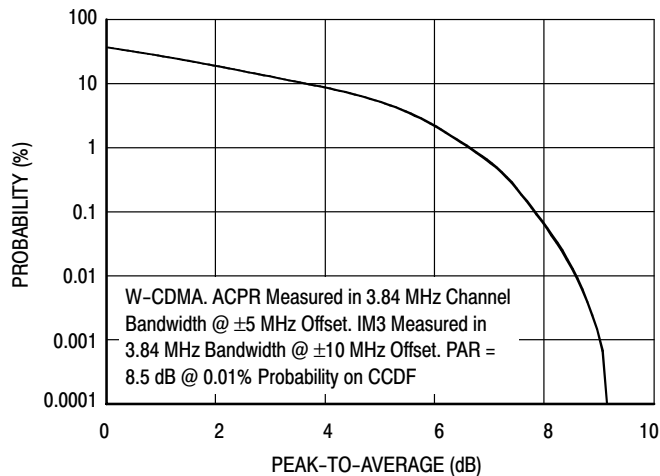


Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

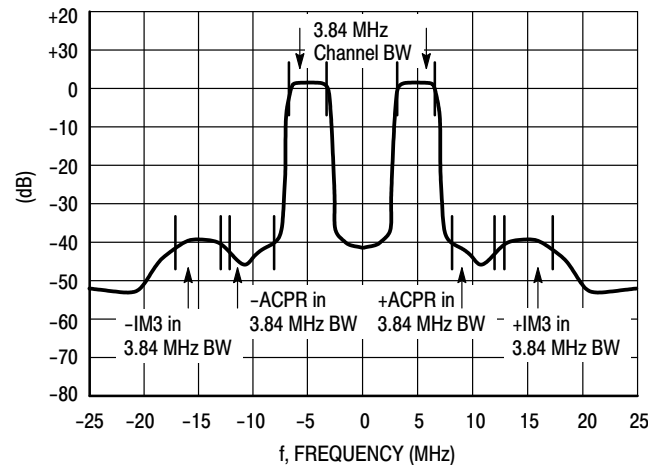
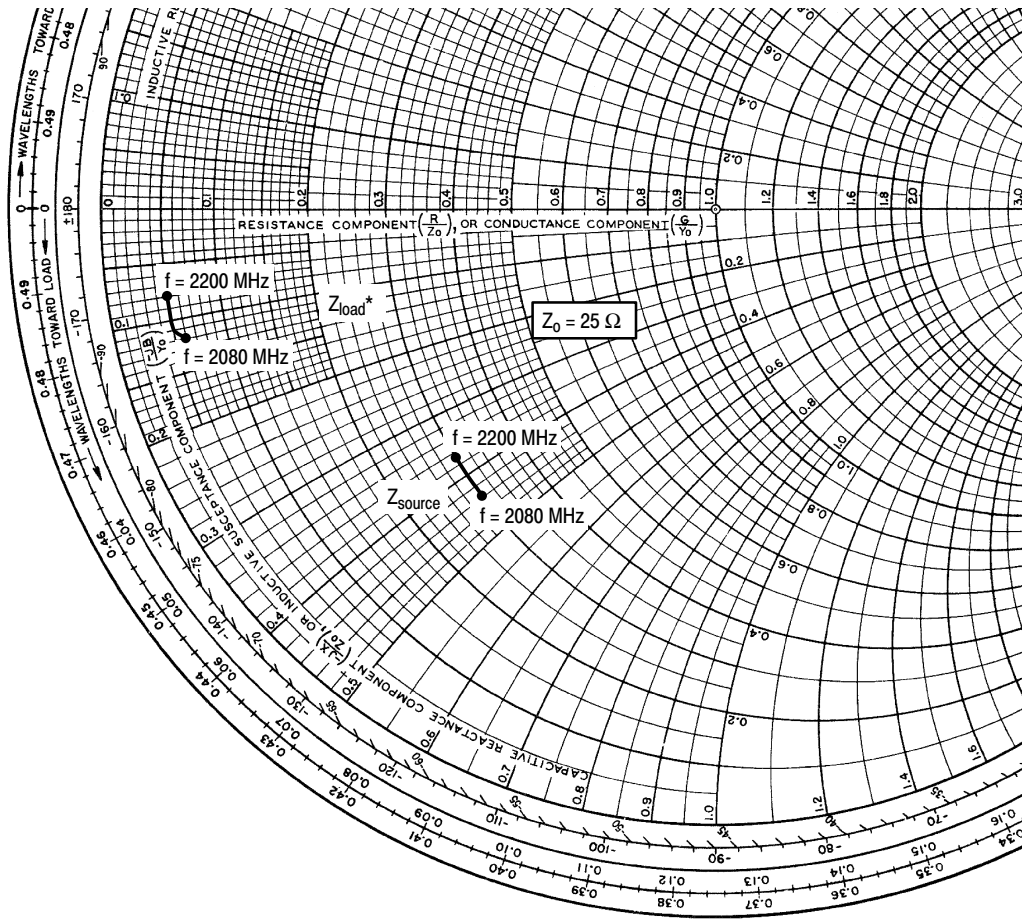


Figure 14. 2-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1200 \text{ mA}$, $P_{out} = 30 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
2080	$7.53 - j10.99$	$1.40 - j3.03$
2110	$7.57 - j10.67$	$1.37 - j2.78$
2140	$7.58 - j10.23$	$1.34 - j2.52$
2170	$7.51 - j9.73$	$1.32 - j2.28$
2200	$7.44 - j9.32$	$1.31 - j2.06$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

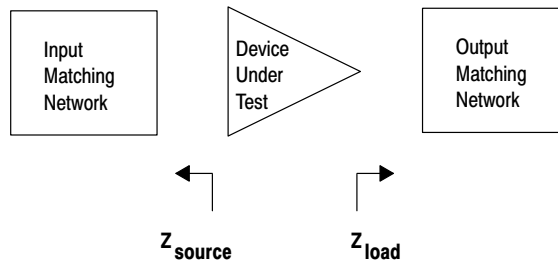


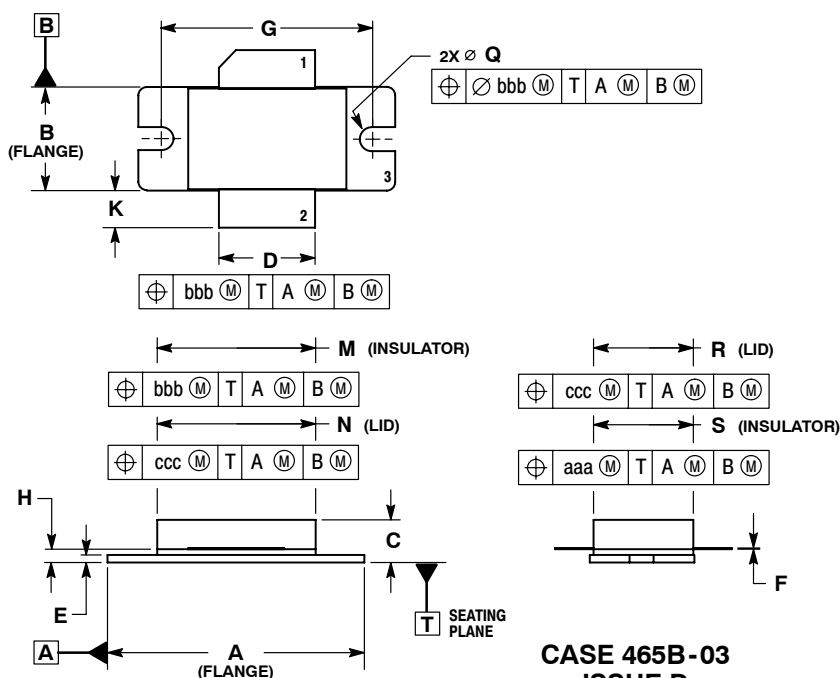
Figure 15. Series Equivalent Source and Load Impedance



NOTES

NOTES

PACKAGE DIMENSIONS

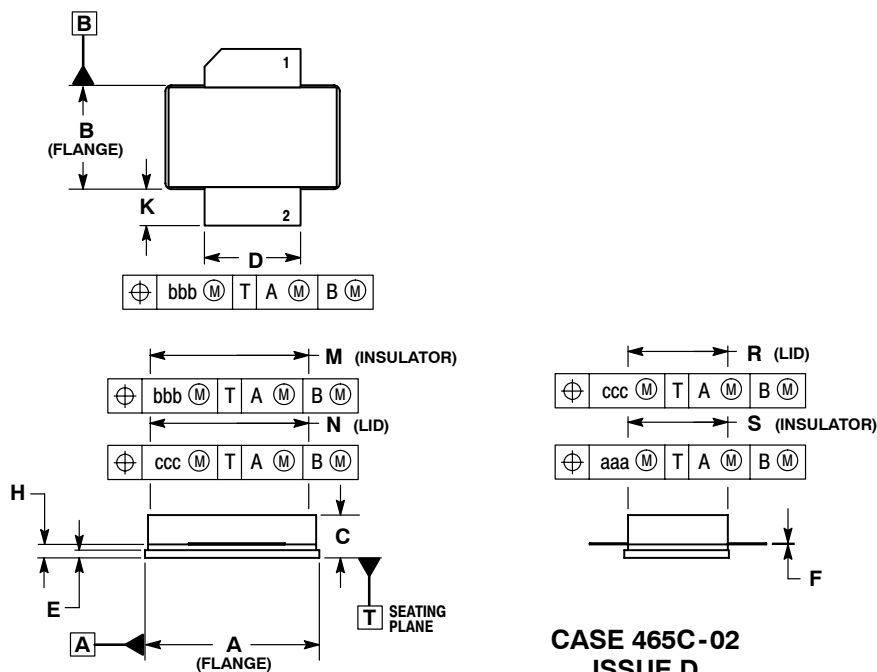


**CASE 465B-03
ISSUE D
NI-880
MRF6S21140HR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. DELETED

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	Ø.118	Ø.138	Ø3.00	Ø3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



**CASE 465C-02
ISSUE D
NI-880S
MRF6S21140HSR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.905	0.915	22.99	23.24
B	0.535	0.545	13.60	13.80
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

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